

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A surface protecting adhesive film for a semiconductor wafer wherein an acrylic adhesive layer having a storage elastic modulus from 1×10^5 Pa to 1×10^7 Pa at 150 °C, an adhesive force from 5g/25mm to 500g/25mm in regard to an SUS304-BA plate whereby the acrylic adhesive layer can be peeled away from a semiconductor wafer surface and a thickness of from 3 to 100 μm is formed on both of a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10 to 200 μm .

2. (Original) The surface protecting adhesive film for a semiconductor wafer according to claim 1, wherein the base film comprises at least one resin film selected from a group consisting of a polyethylene terephthalate, a polyethylene naphthalate, a polyphenylene sulfide and a polyimide.

3. (Currently Amended) A protecting method for a semiconductor wafer in a step of processing a non-circuit-formed surface of a semiconductor wafer comprising a first step of fixing a circuit-formed surface of the semiconductor wafer to a substrate supporting the semiconductor wafer via a surface protecting adhesive film for the semiconductor wafer having an adhesive layer on both a surface and a back

surface of a base film, a second step of fixing a non-circuit-formed surface of the semiconductor wafer on a semiconductor wafer grinding machine via the substrate and mechanically grinding the non-circuit-formed surface of the semiconductor wafer, and a third step of removing a damaged layer generated on the non-circuit-formed surface of the semiconductor wafer in sequence, wherein ~~the surface protecting adhesive film according to claim 1 is used as the surface protecting adhesive film for the semiconductor wafer~~ the adhesive layer of the surface protecting adhesive film has a storage elastic modulus from 1×10^5 Pa to 1×10^7 Pa at 150 °C and a thickness of from 3 to 100 μm and is formed on both of a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10 to 200 μm .

4. (Original) The protecting method for the semiconductor wafer according to claim 3, wherein the third step comprises at least one step selected from a wet etching step, a plasma etching step and a polishing step.